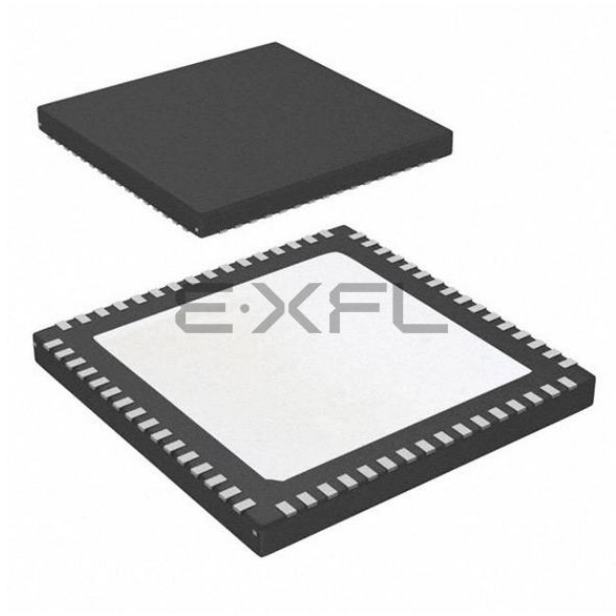

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Number of I/O	51
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Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
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Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
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Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
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Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, peripheral clocks ON	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	13.4	16.6	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	4.7	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	810	—	µA
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	9.4	12.5	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	3.3	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	630	—	µA
Power Mode 1[1,2,3,4]—Full speed with code executing from RAM, LDOs powered by dc-dc at 1.9 V, peripheral clocks OFF	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.3 V	—	7.05	—	mA
		F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz V_{BAT} = 3.8 V	—	6.3	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.3 V	—	2.75	—	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz V_{BAT} = 3.8 V	—	2.6	—	mA
Power Mode 2[1,2,3,4,5]—Core halted with peripheral clocks ON	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	7.6	11.3	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	2.75	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	575	—	µA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2[1,2,3,4,5]—Core halted with only Port I/O clocks on (wake from pin).	I_{BAT}	F_{AHB} = 49 MHz, F_{APB} = 24.5 MHz	—	4	7.2	mA
		F_{AHB} = 20 MHz, F_{APB} = 10 MHz	—	1.47	—	mA
		F_{AHB} = 2.5 MHz, F_{APB} = 1.25 MHz	—	430	—	µA
Power Mode 3[1,2,6]—Fast-Wake Mode (PM3CLKEN = 1)	I_{BAT}	V_{BAT} = 3.8 V	—	320	530	µA
		V_{BAT} = 1.8 V	—	225	—	µA
Power Mode 4[1,2,4,6]—Slower clock speed with code executing from flash, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	385	640	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	330	—	µA
Power Mode 5[1,2,4,6]—Slower clock speed with code executing from RAM, peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	320	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	275	—	µA
Power Mode 6[1,2,4,6]—Core halted with peripheral clocks ON	I_{BAT}	F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 3.8 V	—	315	490	µA
		F_{AHB} = F_{APB} = 16 kHz, V_{BAT} = 1.8 V	—	270	—	µA
Power Mode 8[1,2]—Low Power Sleep, powered through VBAT, VIO, and VIORF at 2.4 V, 32kB of retention RAM	I_{BAT}	RTC Disabled, T_A = 25 °C	—	75	400	nA
		RTC w/ 16.4 kHz LFO, T_A = 25 °C	—	360	—	nA
		RTC w/ 32.768 kHz Crystal, T_A = 25 °C	—	670	—	nA

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.2. Power Consumption (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 8[1,2]—Low Power Sleep, powered by the low power mode charge pump, 32kB of retention RAM	I_{BAT}	RTC w/ 16.4 kHz LFO, V_{BAT} = 2.4 V, T_A = 25 °C	—	180	—	nA
		RTC w/ 32.768 kHz Crystal, V_{BAT} = 2.4 V, T_A = 25 °C	—	300	—	nA
		RTC w/ 16.4 kHz LFO, V_{BAT} = 3.8 V, T_A = 25 °C	—	245	—	nA
		RTC w/ 32.768 kHz Crystal, V_{BAT} = 3.8 V, T_A = 25 °C	—	390	—	nA
Unloaded V_{IO} and V_{IORF} Current[10]	I_{VIO}		—	2	—	nA
Power Mode 8 Peripheral Currents						
UART0	I_{UART0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	195	600	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	120	—	nA
LCD0[7], No segments active	I_{LCD0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	495	660	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	395	—	nA
LCD0[7], All (4 x 40) segments active	I_{LCD0}	V_{BAT} = 3.8 V, T_A = 25 °C	—	800	—	nA
		V_{BAT} = 2.4 V, T_A = 25 °C	—	580	—	nA
Advanced Capture Counter (ACCTR0), LC Single-Ended Mode, Relative to Sampling Frequency[9]	I_{ACCTR}	V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 01	—	1.11	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 01	—	1.44	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 10	—	1.45	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 10	—	1.82	—	nA/Hz
		V_{BAT} = 2.4 V, T_A = 25 °C, CPMD = 11	—	2.15	—	nA/Hz
		V_{BAT} = 3.8 V, T_A = 25 °C, CPMD = 11	—	2.54	—	nA/Hz

Notes:

1. Currents are additive. For example, where I_{BAT} is specified and the mode is not mutually exclusive, enabling the functions increases supply current by the specified amount.
2. Includes all peripherals that cannot have clocks gated in the Clock Control module.
3. Includes LDO and PLL0OSC (>20 MHz) or LPOSC0 (≤20 MHz) supply current.
4. Internal Digital and Memory LDOs scaled to optimal output voltage.
5. Flash AHB clock turned off.
6. Running from internal LFO, Includes LFO supply current.
7. LCD0 current does not include switching currents for external load.
8. IDAC output current not included.
9. Does not include LC tank circuit.
10. Does not include digital drive current or pullup current for active port I/O. Unloaded I_{VIO} is included in all I_{BAT} PM8 production test measurements.

Table 3.3. Power Mode Wake Up Times

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Power Mode 2 or 6 Wake Time	t_{PM2}		4	—	5	clocks
Power Mode 3 Fast Wake Time (using LFO as clock source)	t_{PM3FW}		—	425	—	µs
Power Mode 8 Wake Time	t_{PM8}		—	3.8	—	µs

Notes:
1. Wake times are specified as the time from the wake source to the execution phase of the first instruction following WFI. This includes latency to recognize the wake event and fetch the first instruction (assuming wait states = 0).

Table 3.4. Reset and Supply Monitor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
V_{BAT} High Supply Monitor Threshold (VBATHITHEN = 1)	V_{VBATMH}	Early Warning	—	2.20	—	V
		Reset	1.95	2.05	2.1	V
V_{BAT} Low Supply Monitor Threshold (VBATHITHEN = 0)	V_{VBATML}	Early Warning	—	1.85	—	V
		Reset	1.70	1.75	1.77	V
Power-On Reset (POR) Threshold	V_{POR}	Rising Voltage on V_{BAT}	—	1.4	—	V
		Falling Voltage on V_{BAT}	0.8	1	1.3	V
V_{BAT} Ramp Time	t_{RMP}	Time to $V_{BAT} \geq 1.8$ V	10	—	3000	µs
Reset Delay from POR	t_{POR}	Relative to $V_{BAT} \geq V_{POR}$	3	—	100	ms
Reset Delay from non-POR source	t_{RST}	Time between release of reset source and code execution	—	10	—	µs
$\overline{\text{RESET}}$ Low Time to Generate Reset	t_{RSTL}		50	—	—	ns
Missing Clock Detector Response Time (final rising edge to reset)	t_{MCD}	$F_{AHB} > 1$ MHz	—	0.5	1.5	ms
Missing Clock Detector Trigger Frequency	F_{MCD}		—	2.5	10	kHz
V_{BAT} Supply Monitor Turn-On Time	t_{MON}		—	2	—	µs

Table 3.6. Flash Memory

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Write Time[1]	t_{WRITE}	One 16-bit Half Word	20	21	22	µs
Erase Time[1]	t_{ERASE}	One Page	20	21	22	ms
	t_{ERALL}	Full Device	20	21	22	ms
Endurance (Write/Erase Cycles)	N_{WE}		20k	100k	—	Cycles
Retention[2]	t_{RET}	T_A = 25 °C, 1k Cycles	10	100	—	Years

Notes:
1. Does not include sequencing time before and after the write/erase operation, which may take up to 35 µs. During sequential write operations, this extra time is only taken prior to the first write and after the last write.
2. Additional Data Retention Information is published in the Quarterly Quality and Reliability Report.

Table 3.7. Internal Oscillators

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Phase-Locked Loop (PLL0OSC)						
Calibrated Output Frequency (Free-running output mode, RANGE = 2)	$f_{PLL0OSC}$	Full Temperature and Supply Range	48.3	49	49.7	MHz
Power Supply Sensitivity (Free-running output mode, RANGE = 2)	$PSS_{PLL0OSC}$	T_A = 25 °C, Fout = 49 MHz	—	300	—	ppm/V
Temperature Sensitivity (Free-running output mode, RANGE = 2)	$TS_{PLL0OSC}$	V_{BAT} = 3.3 V, Fout = 49 MHz	—	50	—	ppm/°C
Adjustable Output Frequency Range	$f_{PLL0OSC}$		23	—	50	MHz
Lock Time	$t_{PLL0LOCK}$	f_{REF} = 20 MHz, $f_{PLL0OSC}$ = 50 MHz M=39, N=99, LOCKTH = 0	—	2.75	—	µs
		f_{REF} = 2.5 MHz, $f_{PLL0OSC}$ = 50 MHz M=19, N=399, LOCKTH = 0	—	9.45	—	µs
		f_{REF} = 32.768 kHz, $f_{PLL0OSC}$ = 50 MHz M=0, N=1524, LOCKTH = 0	—	92	—	µs
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{BAT} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{BAT} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{BAT} = 3.3 V	—	0.2	—	%/°C

Table 3.9. SAR ADC

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	N_{bits}	12 Bit Mode		12		Bits
		10 Bit Mode		10		Bits
Supply Voltage Requirements (VBAT)	V_{ADC}	High Speed Mode	2.2	—	3.8	V
		Low Power Mode	1.8	—	3.8	V
Throughput Rate (High Speed Mode)	f_S	12 Bit Mode	—	—	250	ksps
		10 Bit Mode	—	—	1	Msps
Throughput Rate (Low Power Mode)	f_S	12 Bit Mode	—	—	62.5	ksps
		10 Bit Mode	—	—	250	ksps
Tracking Time	t_{TRK}	High Speed Mode	230	—	—	ns
		Low Power Mode	450	—	—	ns
SAR Clock Frequency	f_{SAR}	High Speed Mode	—	—	16.24	MHz
		Low Power Mode	—	—	4	MHz
Conversion Time	t_{CNV}	10-Bit Conversion, SAR Clock = 16 MHz, APB Clock = 40 MHz		762.5		ns
Sample/Hold Capacitor	C_{SAR}	Gain = 1	—	5	—	pF
		Gain = 0.5	—	2.5	—	pF
Input Pin Capacitance	C_{IN}	High Quality Inputs	—	18	—	pF
		Normal Inputs	—	20	—	pF
Input Mux Impedance	R_{MUX}	High Quality Inputs	—	300	—	Ω
		Normal Inputs	—	550	—	Ω
Voltage Reference Range	V_{REF}		1	—	V_{BAT}	V
Input Voltage Range*	V_{IN}	Gain = 1	0	—	V_{REF}	V
		Gain = 0.5	0	—	$2xV_{REF}$	V
Power Supply Rejection Ratio	$PSRR_{ADC}$		—	70	—	dB
DC Performance						
Integral Nonlinearity	INL	12 Bit Mode	—	±1	±1.9	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB
Differential Nonlinearity (Guaranteed Monotonic)	DNL	12 Bit Mode	–1	±0.7	1.8	LSB
		10 Bit Mode	—	±0.2	±0.5	LSB
Offset Error (using VREFGND)	E_{OFF}	12 Bit Mode, VREF = 2.4 V	–2	0	2	LSB
		10 Bit Mode, VREF = 2.4 V	–1	0	1	LSB

Table 3.12. Voltage Reference Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage	V_{REFFS}	–40 to +85 °C, V_{BAT} = 1.8–3.8 V	1.6	1.65	1.7	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{REFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
Internal Precision Reference						
Valid Supply Range	V_{BAT}	VREF2X = 0	1.8	—	3.8	V
		VREF2X = 1	2.7	—	3.8	V
Output Voltage	V_{REFP}	25 °C ambient, VREF2X = 0	1.17	1.2	1.23	V
		25 °C ambient, VREF2X = 1	2.35	2.4	2.45	V
Short-Circuit Current	I_{SC}		—	—	10	mA
Temperature Coefficient	TC_{VREFP}		—	35	—	ppm/°C
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to VREFGND	—	4.5	—	ppm/µA
Load Capacitor	C_{VREFP}	Load = 0 to 200 µA to VREFGND	0.1	—	—	µF
Turn-on Time	$t_{VREFPON}$	4.7 µF tantalum, 0.1 µF ceramic bypass	—	3.8	—	ms
		0.1 µF ceramic bypass	—	200	—	µs
Power Supply Rejection	$PSRR_{VREFP}$	VREF2X = 0	—	320	—	ppm/V
		VREF2X = 1	—	560	—	ppm/V
External Reference						
Input Current	I_{EXTREF}	Sample Rate = 250 ksps; VREF = 3.0 V	—	5.25	—	µA

Table 3.13. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	760	—	mV
Offset Error*	E_{OFF}	T_A = 0 °C	—	±14	—	mV
Slope	M		—	2.77	—	mV/°C
Slope Error*	E_M		—	±25	—	µV/°C
Linearity			—	1	—	°C
Turn-on Time			—	1.8	—	µs

***Note:** Absolute input pin voltage is limited by the lower of the supply at VBAT and VIO.

Table 3.14. Comparator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Response Time, CMPMD = 00 (Highest Speed)	t_{RESP0}	+100 mV Differential	—	100	—	ns
		–100 mV Differential	—	150	—	ns
Response Time, CMPMD = 11 (Lowest Power)	t_{RESP3}	+100 mV Differential	—	1.4	—	µs
		–100 mV Differential	—	3.5	—	µs
Positive Hysteresis Mode 0 (CPMD = 00)	HYS_{CP+}	CMPHYP = 00	—	0.37	—	mV
		CMPHYP = 01	—	7.9	—	mV
		CMPHYP = 10	—	16.7	—	mV
		CMPHYP = 11	—	32.8	—	mV
Negative Hysteresis Mode 0 (CPMD = 00)	HYS_{CP-}	CMPHYN = 00	—	0.37	—	mV
		CMPHYN = 01	—	–7.9	—	mV
		CMPHYN = 10	—	–16.1	—	mV
		CMPHYN = 11	—	–32.7	—	mV
Positive Hysteresis Mode 1 (CPMD = 01)	HYS_{CP+}	CMPHYP = 00	—	0.47	—	mV
		CMPHYP = 01	—	5.85	—	mV
		CMPHYP = 10	—	12	—	mV
		CMPHYP = 11	—	24.4	—	mV
Negative Hysteresis Mode 1 (CPMD = 01)	HYS_{CP-}	CMPHYN = 00	—	0.47	—	mV
		CMPHYN = 01	—	–6.0	—	mV
		CMPHYN = 10	—	–12.1	—	mV
		CMPHYN = 11	—	–24.6	—	mV
Positive Hysteresis Mode 2 (CPMD = 10)	HYS_{CP+}	CMPHYP = 00	—	0.66	—	mV
		CMPHYP = 01	—	4.55	—	mV
		CMPHYP = 10	—	9.3	—	mV
		CMPHYP = 11	—	19	—	mV
Negative Hysteresis Mode 2 (CPMD = 10)	HYS_{CP-}	CMPHYN = 00	—	0.6	—	mV
		CMPHYN = 01	—	–4.5	—	mV
		CMPHYN = 10	—	–9.5	—	mV
		CMPHYN = 11	—	–19	—	mV

4.1. Power

The SiM3L1xx devices include a dc-dc buck converter that can take an input from 1.8–3.8 V and create an output from 1.25–3.8 V. In addition, SiM3L1xx devices include three low dropout regulators as part of the LDO0 module: one LDO powers the analog subsystems, one LDO powers the flash and SRAM memory at 1.8 V, and one LDO powers the digital and core circuitry. Each of these regulators can be independently powered from the dc-dc converter or directly from the battery voltage, and their outputs are adjustable to conserve system power. SiM3L1xx devices also include a low power charge pump in the PMU module for use in low power modes (PM8) to further reduce the power consumption of the device.

Figure 4.2 shows the power system configuration of these devices.

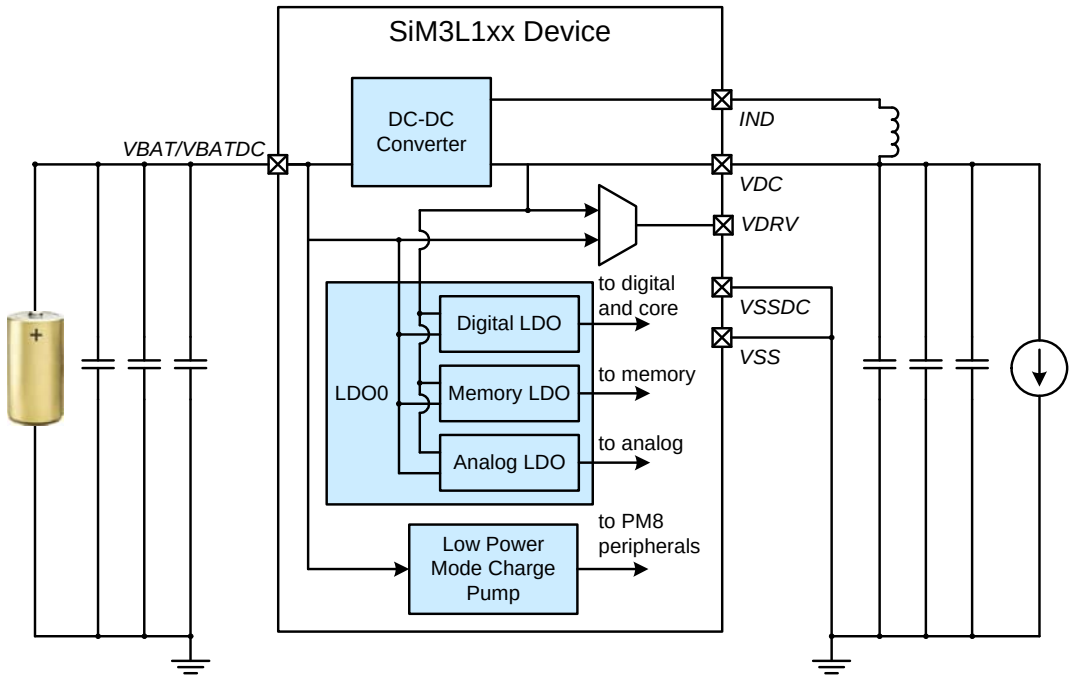

Figure 4.2. SiM3L1xx Power

4.1.1. DC-DC Buck Converter (DCDC0)

SiM3L1xx devices include an on-chip step-down dc-dc converter to efficiently utilize the energy stored in the battery, thus extending the operational life time. The dc-dc converter is a switching buck converter with a programmable output voltage that should be at least 0.45 V lower than the input battery voltage; if this criteria is not met and the converter can no longer operate, the output of the dc-dc converter automatically connects to the battery. The dc-dc converter can supply up to 100 mA and can be used to power the MCU and/or external devices in the system.

The dc-dc converter has a built in voltage reference and oscillator and will automatically limit or turn off the switching activity in case the peak inductor current rises beyond a safe limit or the output voltage rises above the programmed target value. This allows the dc-dc converter output to be safely overdriven by a secondary power source (when available) in order to preserve battery life. When enabled, the dc-dc converter can source current into the output capacitor, but cannot sink current.

The dc-dc converter includes the following features:

- Efficiently utilizes the energy stored in a battery, extending its operational lifetime.
- Input range: 1.8 to 3.8 V.
- Output range: 1.25 to 3.8 V in 50 mV (1.25–1.8 V) or 100 mV (1.8–3.8 V) steps.
- Supplies up to 100 mA.
- Includes a voltage reference and an oscillator.

4.1.5.6. Power Mode Summary

The power modes described above are summarized in Table 4.1. Table 3.2 and Table 3.3 provide more information on the power consumption and wake up times for each mode.

Table 4.1. SiM3L1xx Power Modes

Mode	Description	Notes
Normal	■ Core operating at full speed ■ Code executing from flash	■ Full device operation
Power Mode 1 (PM1)	■ Core operating at full speed ■ Code executing from RAM	■ Full device operation ■ Higher CPU bandwidth than PM0 (RAM can operate with zero wait states at any frequency)
Power Mode 2 (PM2)	■ Core halted ■ AHB, APB and all peripherals operational at full speed	■ Fast wakeup from any interrupt source
Power Mode 3 (PM3)	■ All clocks to core and peripherals stopped ■ Faster wake enabled by keeping LFOSC0 or RTC0TCLK active	■ Wake on any wake source or reset source defined in the PMU
Power Mode 4 (PM4)	■ Core operating at low speed ■ Code executing from flash	■ Same capabilities as PM0, operating at lower speed ■ Lower clock speed enables lower LDO output settings to save power
Power Mode 5 (PM5)	■ Core operating at low speed ■ Code executing from RAM	■ Same capabilities as PM1, operating at lower speed ■ Lower clock speed enables lower LDO output settings to save power
Power Mode 6 (PM6)	■ Core halted ■ AHB, APB and all peripherals operational at low speed	■ Same capabilities as PM2, operating at lower speed ■ Lower clock speed enables lower LDO output settings to save power ■ When running from LFOSC0, power is similar to PM3, but the device wakes much faster
Power Mode 8 (PM8)	■ Low power sleep ■ LDO regulators are disabled and all active circuitry operates directly from VBAT ■ The following functions are available: ACCTR0, RTC0, UART0 running from RTC0TCLK, LPTIMER0, port match, and the LCD controller ■ Register and RAM state retention	■ Lowest power consumption ■ Wake on any wake source or reset source defined in the PMU

4.5. Data Peripherals

4.5.1. 10-Channel DMA Controller

The DMA facilitates autonomous peripheral operation, allowing the core to finish tasks more quickly without spending time polling or waiting for peripherals to interrupt. This helps reduce the overall power consumption of the system, as the device can spend more time in low-power modes.

The DMA controller has the following features:

- Utilizes ARM PrimeCell uDMA architecture.
- Implements 10 channels.
- DMA crossbar supports DTM0, DTM1, DTM2, SARADC0, IDAC0, I2C0, SPI0, SPI1, USART0, AES0, ENCDEC0, EPCA0, external pin triggers, and timers.
- Supports primary, alternate, and scatter-gather data structures to implement various types of transfers.
- Access allowed to all AHB and APB memory space.

4.5.2. Data Transfer Managers (DTM0, DTM1, DTM2)

The Data Transfer Manager is a module that collects DMA request signals from various peripherals and generates a series of master DMA requests based on a state-driven configuration. This master request drives a set of DMA channels to perform functions such as assembling and transferring communication packets to external devices. This capability saves power by allowing the core to remain in a low power mode during complex transfer operations. A combination of simple and peripheral scatter-gather DMA configurations can be used to perform complex operations while reducing memory requirements.

The DTM acts as a side channel for the peripheral's DMA control signals. When active, it manages the DMA control signals for the peripherals. When the DTMn module is inactive, the peripherals communicate directly to the DMA module.

The DTMn module has the following features:

- State descriptions stored in RAM with up to 15 states supported per module.
- Supports up to 15 source peripherals and up to 15 destination peripherals per module, in addition to memory or peripherals that do not require a data request.
- Includes error detection and an optional transfer timeout.
- Includes notifications for state transitions.

4.5.3. 128/192/256-bit Hardware AES Encryption (AES0)

The basic AES block cipher is implemented in hardware. The integrated hardware support for Cipher Block Chaining (CBC) and Counter (CTR) algorithms results in identical performance, memory bandwidth, and memory footprint between the most basic Electronic Codebook (ECB) algorithm and these more complex algorithms. This hardware accelerator translates to more core bandwidth available for other functions or a power savings for low-power applications.

The AES module includes the following features:

- Operates on 4-word (16-byte) blocks.
- Supports key sizes of 128, 192, and 256 bits for both encryption and decryption.
- Generates the round key for decryption operations.
- All cipher operations can be performed without any firmware intervention for multiple 4-word blocks (up to 32 kB).
- Support for various chained and stream-ciphering configurations with XOR paths on both the input and output.
- Internal 4-word FIFOs to facilitate DMA operations.
- Integrated key storage.
- Hardware acceleration for Electronic Codebook (ECB), Cipher-Block Chaining (CBC), and Counter (CTR) algorithms utilizing integrated counterblock generation and previous-block caching.

4.5.4. 16/32-bit Enhanced CRC (ECRC0)

The ECRC module is designed to provide hardware calculations for flash memory verification and communications protocols. In addition to calculating a result from direct writes from firmware, the ECRC module can automatically snoop the APB bus and calculate a result from data written to or read from a particular peripheral. This allows for an automatic CRC result without directly feeding data through the ECRC module.

The supported 32-bit polynomial is 0x04C11DB7 (IEEE 802.3). The 16-bit polynomial is fully programmable.

The ECRC module includes the following features:

- Support for a programmable 16-bit polynomial and one fixed 32-bit polynomial.
- Byte-level bit reversal for the CRC input.
- Byte-order reorientation of words for the CRC input.
- Word or half-word bit reversal of the CRC result.
- Ability to configure and seed an operation in a single register write.
- Support for single-cycle parallel (unrolled) CRC computation for 32-, 16-, or 8-bit blocks.
- Capability to CRC 32 bits of data per peripheral bus (APB) clock.
- Automatic APB bus snooping.
- Support for DMA writes using firmware request mode.

4.5.5. Encoder / Decoder (ENCDEC0)

The encoder / decoder module supports Manchester and Three-out-of-Six encoding and decoding from either firmware or DMA operations.

This module has the following features:

- Supports Manchester and Three-out-of-Six encoding and decoding.
- Automatic flag clearing when writing the input or reading the output data registers.
- Writing to the input data register automatically initiates an encode or decode operation.
- Optional output in one’s complement format.
- Hardware error detection for invalid input data during decode operations, which helps reduce power consumption and packet turn-around time.
- Flexible byte swapping on the input or output data.

Table 6.1. Pin Definitions and Alternate Functions for SiM3L1x7

Pin Name	Type	Pin Numbers (TQFP-80)	I/O Voltage Domain	Crossbar Capability	Port Match	LCD Interface	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
VSS	Ground	12 31 52 71							
VSSDC	Ground (DC-DC)	12							
VIO	Power (I/O)	7 30 68							
VIORF	Power (RF I/O)	8							
VBAT/ VBATDC		10							
VDRV		9							
VDC		13							
VLCD	Power (LCD Charge Pump)	67							
IND	DC-DC Inductor	11							
$\overline{\text{RESET}}$	Active-low Reset	72							
TCK/ SWCLK	JTAG / Serial Wire	6							
TMS/ SWDIO	JTAG / Serial Wire	5							
RTC1	RTC Oscillator Input	70							
RTC2	RTC Oscillator Output	69							

Table 6.1. Pin Definitions and Alternate Functions for SiM3L1x7 (Continued)

Pin Name	Type	Pin Numbers (TQFP-80)	I/O Voltage Domain	Crossbar Capability	Port Match	LCD Interface	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
PB0.9	Standard I/O	75	VIO	✓	✓		✓	LPT0T1 INT0.9 WAKE.9 ACCTR0_LCPUL0	ADC0.1 CMP0N.1
PB0.10	Standard I/O	74	VIO	✓	✓		✓	LPT0T2 INT0.10 WAKE.10 ACCTR0_LCPUL1	ADC0.2 CMP1P.1
PB0.11/ TDO/SWV	Standard I/O / JTAG / Serial Wire Viewer	73	VIO	✓	✓		✓	LPT0T3 LPT0OUT1 INT0.11 WAKE.11	ADC0.3 CMP1N.1
PB1.0	Standard I/O	66	VIO	✓	✓	LCD0.39		LPT0T4 INT0.12 ACCTR0_LCBIAS0	CMP0P.2
PB1.1	Standard I/O	65	VIO	✓	✓	LCD0.38		LPT0T5 INT0.13 ACCTR0_LCBIAS1	CMP0N.2
PB1.2	Standard I/O	64	VIO	✓	✓	LCD0.37		LPT0T6 INT0.14 UART0_TX	CMP1P.2
PB1.3	Standard I/O	63	VIO	✓	✓	LCD0.36		LPT0T7 INT0.15 UART0_RX	CMP1N.2
PB1.4	Standard I/O	62	VIO	✓	✓	LCD0.35		ACCTR0_DBG0	ADC0.4
PB1.5	Standard I/O	61	VIO	✓	✓	LCD0.34		ACCTR0_DBG1	ADC0.5
PB1.6/TDI	Standard I/O / JTAG	60	VIO	✓	✓	LCD0.33			ADC0.6
PB1.7	Standard I/O	59	VIO	✓	✓	LCD0.32		RTC0TCLK_OUT	ADC0.7

Table 6.2. Pin Definitions and Alternate Functions for SiM3L1x6 (Continued)

Pin Name	Type	Pin Numbers	I/O Voltage Domain	Crossbar Capability	Port Match	LCD Interface	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
PB1.1	Standard I/O	52	VIO	XBR0	✓	LCD0.30		LPT0T5 INT0.13 ACCTR0_LCBIAS1	CMP0N.2
PB1.2	Standard I/O	51	VIO	XBR0	✓	LCD0.29		LPT0T6 INT0.14 UART0_TX	CMP1P.2
PB1.3	Standard I/O	50	VIO	XBR0	✓	LCD0.28		LPT0T7 INT0.15 UART0_RX	CMP1N.2
PB1.4	Standard I/O	49	VIO	XBR0	✓	LCD0.27		ACCTR0_DBG0	ADC0.3
PB1.5	Standard I/O	48	VIO	XBR0	✓	LCD0.26		ACCTR0_DBG1	ADC0.4
PB1.6	Standard I/O	47	VIO	XBR0	✓	LCD0.25		RTC0TCLK_OUT	ADC0.5
PB1.7	Standard I/O	46	VIO	XBR0	✓	LCD0.24			CMP0P.3
PB1.8	Standard I/O	45	VIO	XBR0	✓	LCD0.23			CMP0N.3
PB1.9	Standard I/O	44	VIO	XBR0	✓	LCD0.22			CMP1P.3
PB1.10	Standard I/O	43	VIO	XBR0	✓	LCD0.21			CMP1N.3
PB2.0	Standard I/O	42	VIORF	XBR0	✓			LPT0T8 INT1.0 WAKE.12 SPI1_CTS	ADC0.6 CMP0P.4
PB2.4	Standard I/O	40	VIORF	XBR0	✓			LPT0T12 INT1.4 SPI1_SCLK	ADC0.7 CMP0P.5

Table 6.3. Pin Definitions and Alternate Functions for SiM3L1x4 (Continued)

Pin Name	Type	Pin Numbers	I/O Voltage Domain	Crossbar Capability	Port Match	Output Toggle Logic	External Trigger Inputs / Digital Functions	Analog Functions
PB2.1	Standard I/O	28	VIORF	XBR0	✓		LPT0T9 INT1.1 WAKE.13 VIORFCLK	ADC0.3 CMP0N.4
PB2.2	Standard I/O	27	VIORF	XBR0	✓		LPT0T10 INT1.2 WAKE.14	ADC0.4 CMP1P.4
PB2.3	Standard I/O	26	VIORF	XBR0	✓		LPT0T11 INT1.3 WAKE.15	ADC0.5 CMP1N.4
PB2.4	Standard I/O	24	VIORF	XBR0	✓		LPT0T12 INT1.4 SPI1_SCLK	ADC0.6 CMP0P.5
PB2.5	Standard I/O	23	VIORF	XBR0	✓		LPT0T13 INT1.5 SPI1_MISO	ADC0.7 CMP0N.5
PB2.6	Standard I/O	22	VIORF	XBR0	✓		LPT0T14 INT1.6 SPI1_MOSI	ADC0.8 CMP1P.5
PB2.7	Standard I/O	21	VIORF	XBR0	✓		INT1.7 SPI1_NSS	ADC0.9 CMP1N.5
PB3.0	Standard I/O	20	VIO	XBR0	✓		INT1.8	CMP0N.7
PB3.1	Standard I/O	19	VIO	XBR0	✓		INT1.9	CMP1P.7
PB3.2	Standard I/O	18	VIO	XBR0	✓		INT1.10	CMP1N.7
PB3.3	Standard I/O	17	VIO	XBR0	✓		INT1.11	ADC0.10
PB3.4	Standard I/O	16	VIO	XBR0	✓		INT1.12	ADC0.11
PB3.5	Standard I/O	15	VIO	XBR0	✓		INT1.13	ADC0.12

6.5. QFN-64 Package Specifications

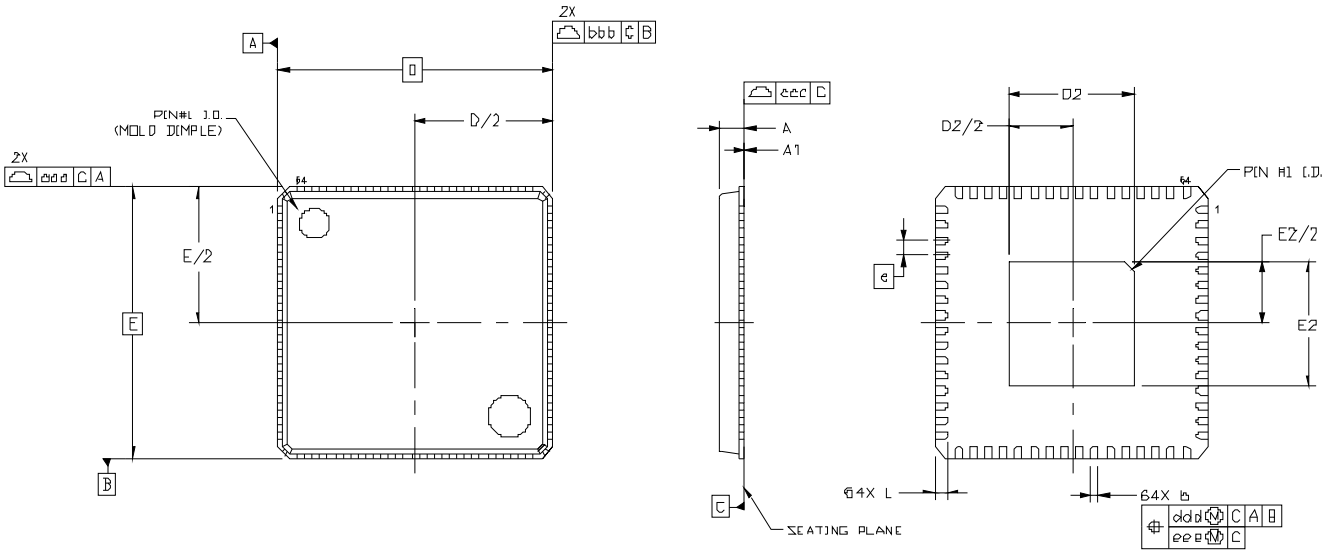

Figure 6.7. QFN-64 Package Drawing

Table 6.6. QFN-64 Package Dimensions

Dimension	Min	Nominal	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D		9.00 BSC	
D2	3.95	4.10	4.25
e		0.50 BSC	
E		9.00 BSC	
E2	3.95	4.10	4.25
L	0.30	0.40	0.50
aaa		0.10	
bbb		0.10	
ccc		0.08	
ddd		0.10	
eee		0.05	

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MO-220.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6.7. QFN-40 Package Specifications

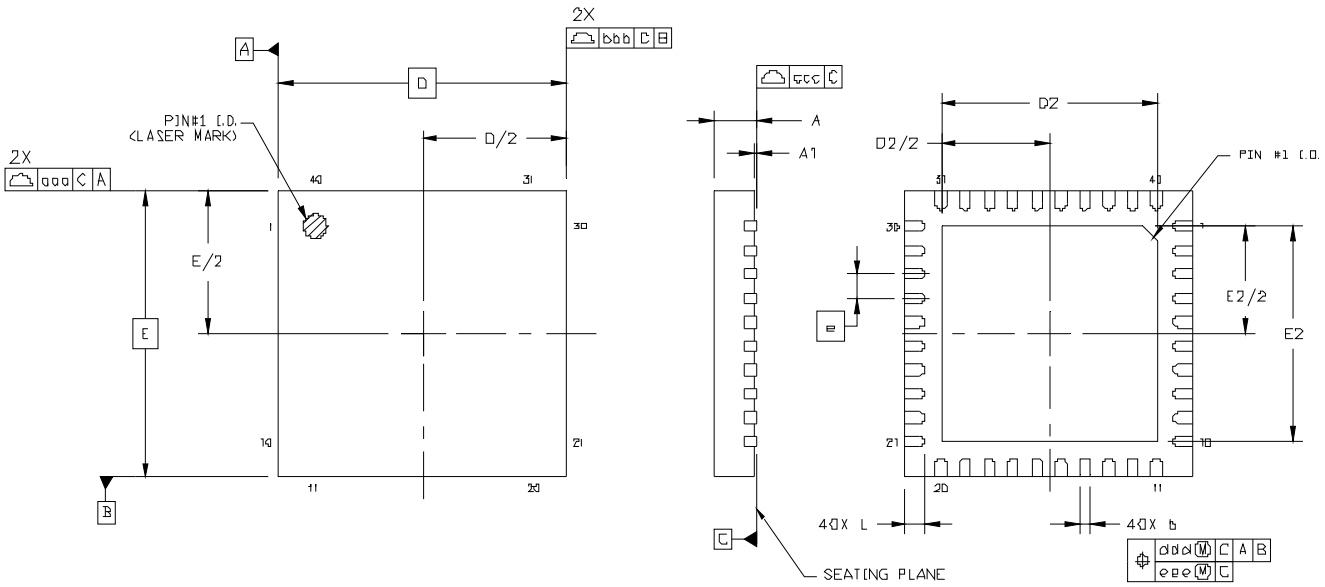

Figure 6.11. QFN-40 Package Drawing

Table 6.10. QFN-40 Package Dimensions

Dimension	Min	Nominal	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D		6.00 BSC	
D2	4.35	4.50	4.65
e		0.50 BSC	
E		6.00 BSC	
E2	4.35	4.5	4.65
L	0.30	0.40	0.50
aaa		0.10	
bbb		0.10	
ccc		0.08	
ddd		0.10	
eee		0.05	

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MO-220.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

7. Revision Specific Behavior

This chapter describes any differences between released revisions of the device.

7.1. Revision Identification

The Lot ID Code on the top side of the device package can be used for decoding device revision information. Figures 7.1, 7.2, and 7.3 show how to find the Lot ID Code on the top side of the device package.

In addition, firmware can determine the revision of the device by checking the DEVICEID registers.

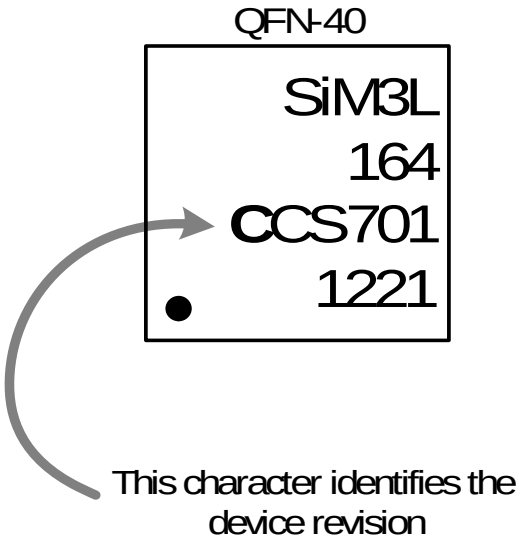

Figure 7.1. SiM3L1x7-GQ Revision Information

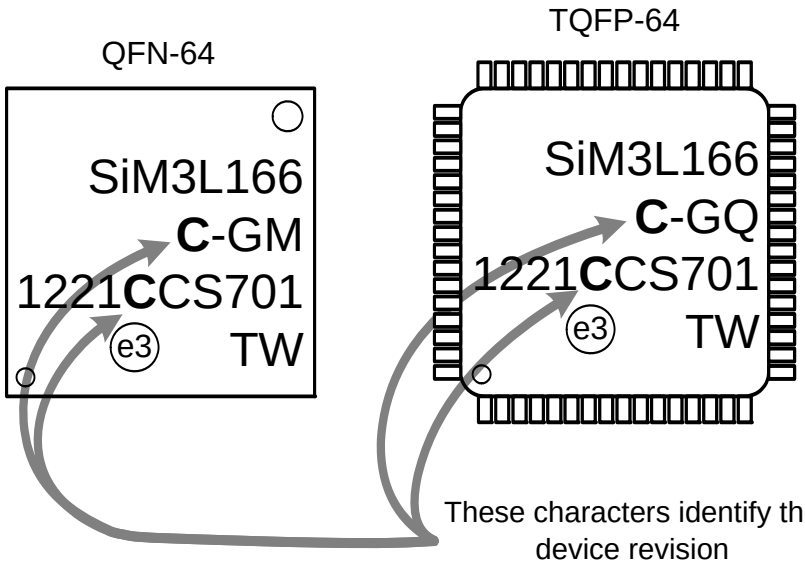

Figure 7.2. SiM3L1x6-GM and SiM3L1x6-GQ Revision Information